

一、 描述 / Descriptions

VRW056 硅 NPN 三极管 SOT-23 封装 Silicon NPN transistor in a SOT-23 Plastic Package.

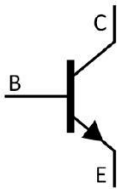
二、 特性 / Features

高电压，高电流，高 h_{FE} ，低噪声，优异的 h_{FE} 线性度，符合 AEC-Q101 标准，高可靠性，HF 产品。

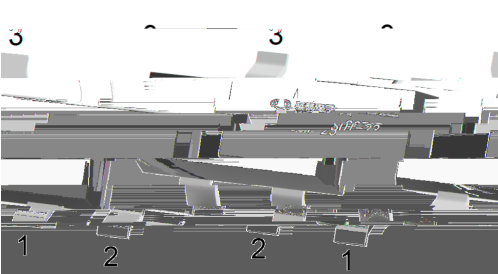
三、 应用 / Applications

音频频率通用放大器应用，满足汽车应用的要求。

四、 等效电路 / Equivalent Circuit



五、 引脚 / Pinning



PIN1 基极 Base PIN 2 发射极 Emitter PIN 3 集电极 Collector

六、 h_{FE} 分类及标识 / h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y	GR	BL
h_{FE} Range	70 140	120 240	200 400	350 700
Marking	QLO	QLY	QLG	QLL



Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=2.0mA$	70		700	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.1	0.25	V

4. L^{∞}



ب"خ

$$\tau \chi \quad \mathbb{H} \cap \mathbb{Z} \dot{\eta} \quad \mathbb{F} \beta \% \mathbb{V}^{\xi}$$
$$0\chi \quad \mathbb{H} \mathfrak{z}^N \Gamma \mathfrak{d}$$
$$R_X \quad \text{h}_{FE} \quad 6 \quad K\Omega$$

Note:

T= Dxwr p r eloh kdor j hq0iuhh sur gxfw Fr gh

0X Product Type Code

R_χ h_{FE} Classifications Symbol

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0luhh,

ب " Χ

Note:

1. Preheating: 150~200 °C, Time: 60~120sec.
2. Peak Temp.: 255 °C, Duration: 5~0.5sec.
3. Cooling Speed: 2~10 °C/sec.

Resistance to Soldering Heat Test Conditions

Temp.: 260±5 °C Time: 10±1 sec.

Packaging SPEC.

REEL

Package Type	Units				Dimension	(unit mm ³)
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box		